

TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (U-MOSVI-H)

# TPC8216-H

High Efficiency DC-DC Converter Applications

Notebook PC Applications

Portable-Equipment Applications

- Small footprint due to a small and thin package
- High-speed switching
- Small gate charge:  $Q_{SW} = 3.4$  nC (typ.)
- Low drain-source ON-resistance:  $R_{DS(ON)} = 13.6$  m $\Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 19$  S (typ.)
- Low leakage current:  $I_{DSS} = 10$   $\mu$ A (max) ( $V_{DS} = 30$  V)
- Enhancement mode:  $V_{th} = 1.3$  to  $2.3$  V ( $V_{DS} = 10$  V,  $I_D = 0.1$  mA)

## Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

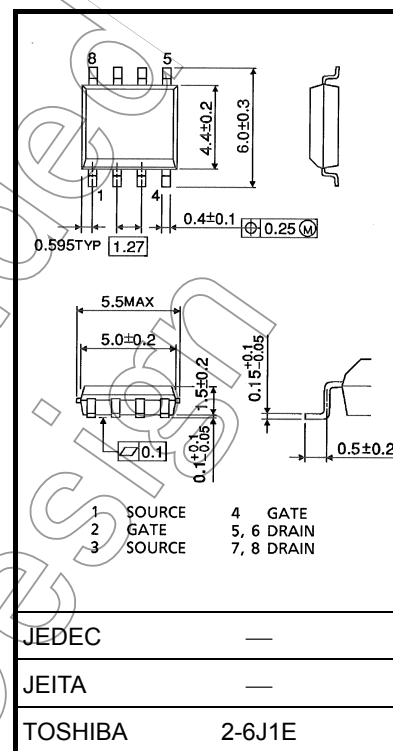
Characteristic		Symbol	Rating	Unit
Drain-source voltage		$V_{DSS}$	30	V
Drain-gate voltage ( $R_{GS} = 20$ k $\Omega$ )		$V_{DGR}$	30	V
Gate-source voltage		$V_{GSS}$	$\pm 20$	V
Drain current	D C (Note 1)	$I_D$	6.4	A
	Pulse (Note 1)	$I_{DP}$	25.6	
Drain power dissipation ( $t = 10$ s) (Note 2a)	Single-device operation (Note 3a)	$P_D(1)$	1.5	W
	Single-device value at dual operation (Note 3b)	$P_D(2)$	1.1	
Drain power dissipation ( $t = 10$ s) (Note 2b)	Single-device operation (Note 3a)	$P_D(1)$	0.75	W
	Single-device value at dual operation (Note 3b)	$P_D(2)$	0.45	
Single-pulse avalanche energy (Note 4)		$E_{AS}$	53	mJ
Avalanche current		$I_{AR}$	6.4	A
Repetitive avalanche energy (Note 2a, Note 3b, Note 5)		$E_{AR}$	0.13	mJ
Channel temperature		$T_{ch}$	150	$^\circ\text{C}$
Storage temperature range		$T_{stg}$	-55 to 150	$^\circ\text{C}$

Note: For Notes 1 to 4, refer to the next page.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating" Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

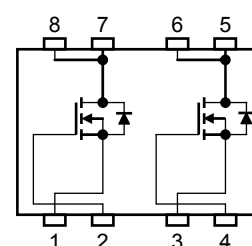
This transistor is an electrostatic-sensitive device. Handle with care.

Unit: mm



Weight: 0.085 g (typ.)

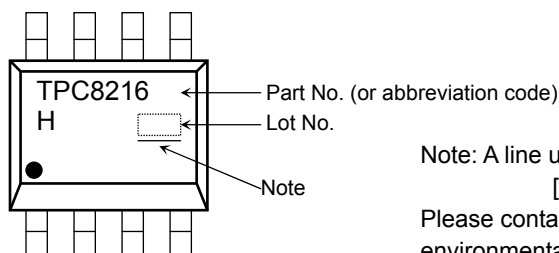
## Circuit Configuration



## Thermal Characteristics

Characteristic		Symbol	Max	Unit
Thermal resistance, channel to ambient ( $t = 10$ s)	Single-device operation (Note 3a)	$R_{th (ch-a) (1)}$	83.3	°C/W
	Single-device value at dual operation (Note 3b)	$R_{th (ch-a) (2)}$	114	
Thermal resistance, channel to ambient ( $t = 10$ s)	Single-device operation (Note 3a)	$R_{th (ch-a) (1)}$	167	
	Single-device value at dual operation (Note 3b)	$R_{th (ch-a) (2)}$	278	

## Marking

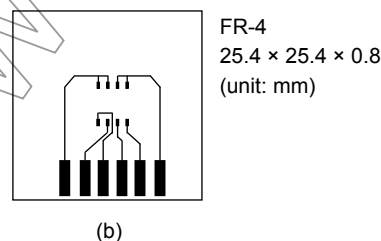
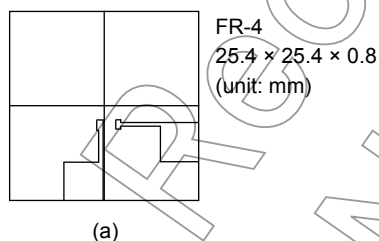


Note: A line under a Lot No. identifies the indication of product Labels.  
[[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is the Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a) (b) Device mounted on a glass-epoxy board (b)



Note 3:

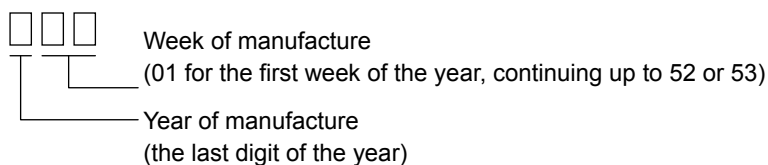
- The power dissipation and thermal resistance values are shown for a single device (During single-device operation, power is only applied to one device.)
- The power dissipation and thermal resistance values are shown for a single device (During dual operation, power is evenly applied to both devices.)

Note 4:  $V_{DD} = 24$  V,  $T_{ch} = 25^{\circ}\text{C}$  (Initial),  $L = 1.0$  mH,  $R_G = 25$   $\Omega$ ,  $I_{AR} = 6.4$  A

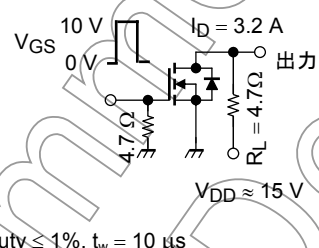
Note 5: Repetitive rating: pulse width limited by maximum channel temperature

Note 6: • on the lower left of the marking indicates Pin 1.

\* Weekly code: (three digits)

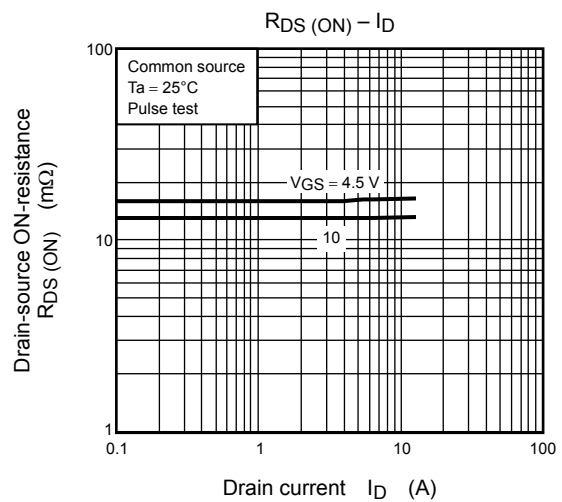
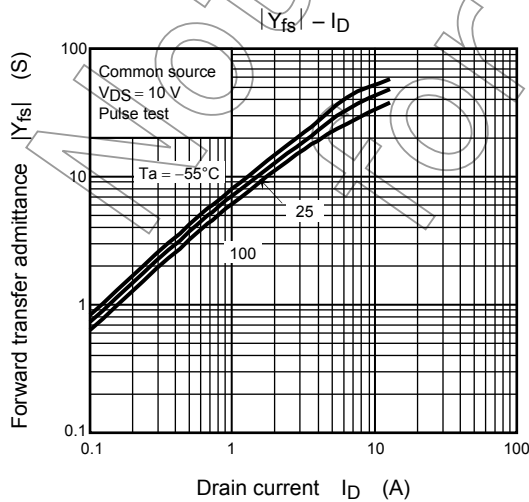
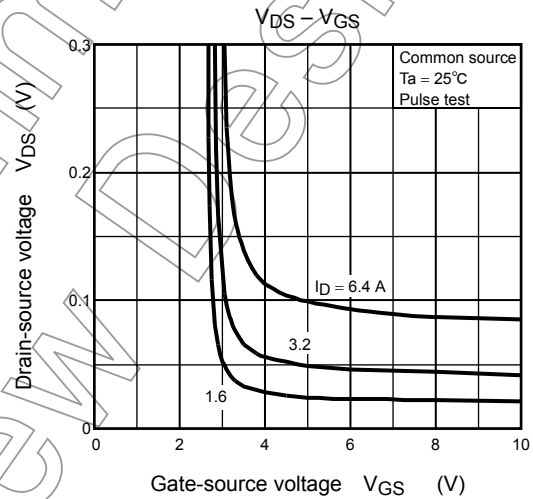
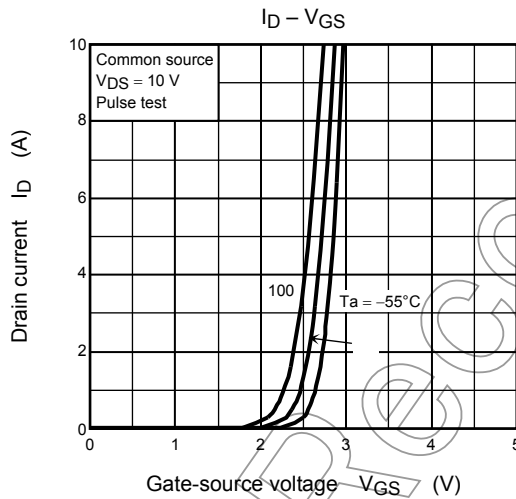
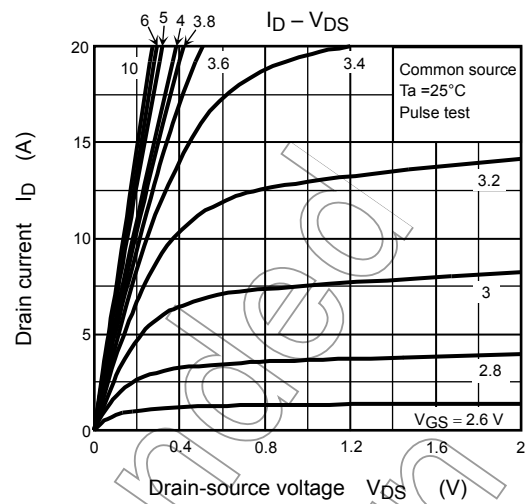
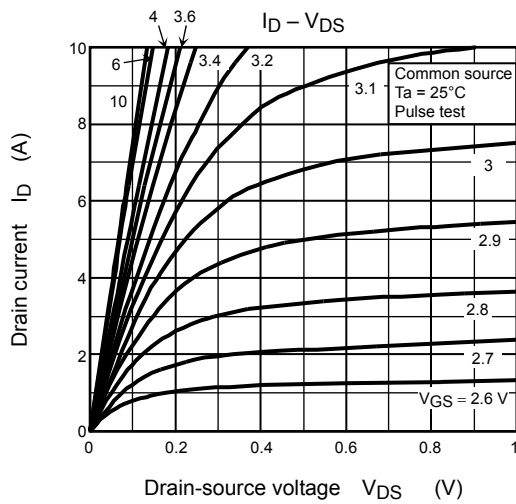


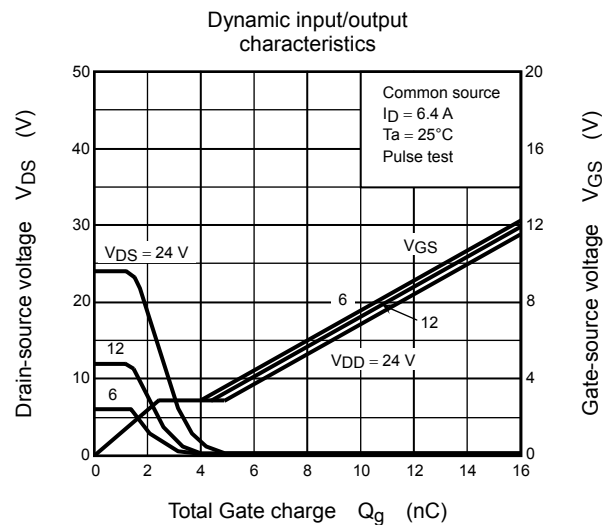
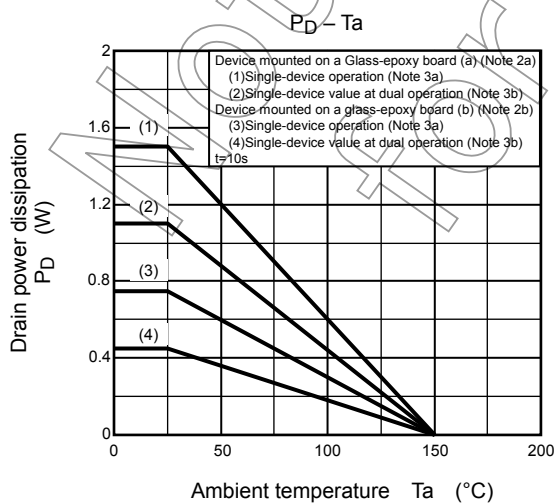
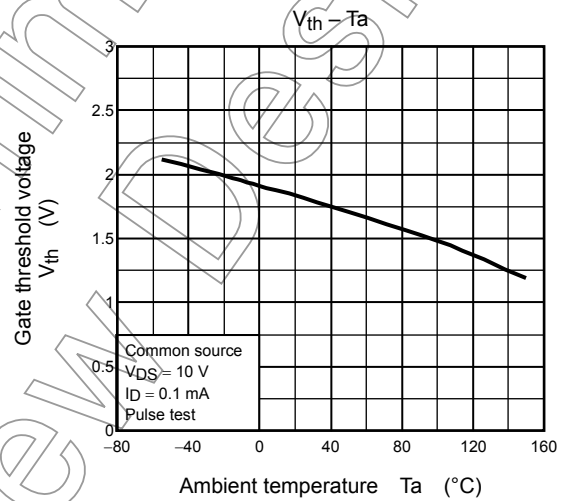
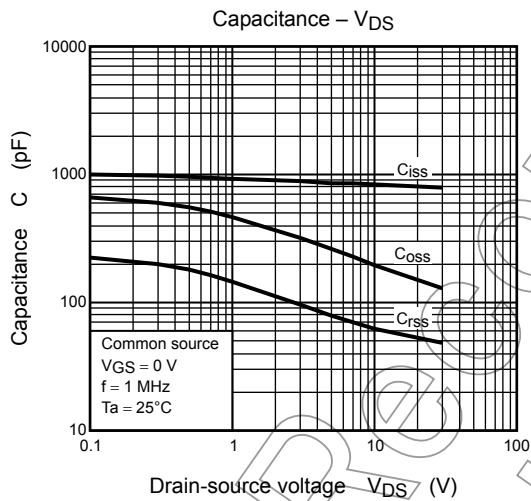
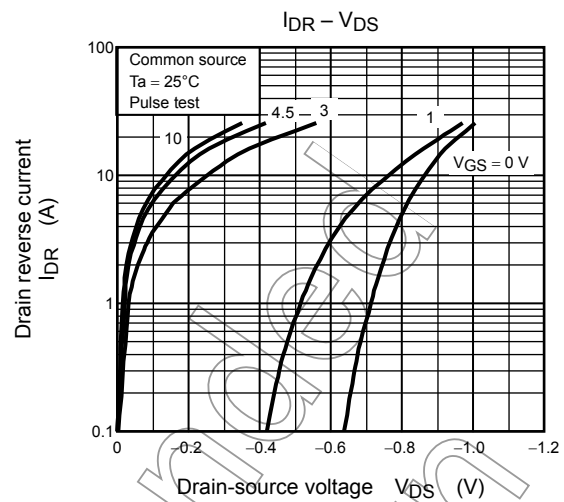
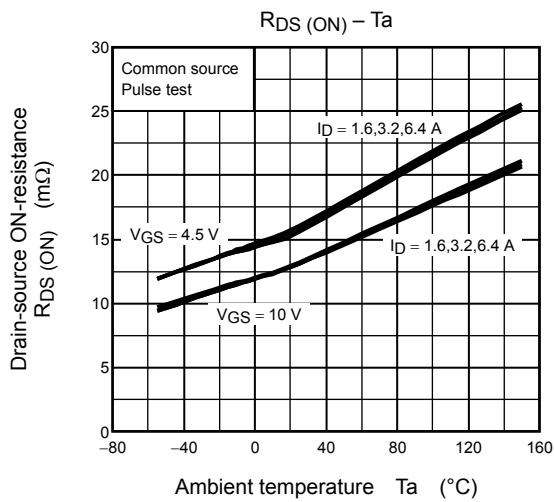
## Electrical Characteristics (Ta = 25°C)

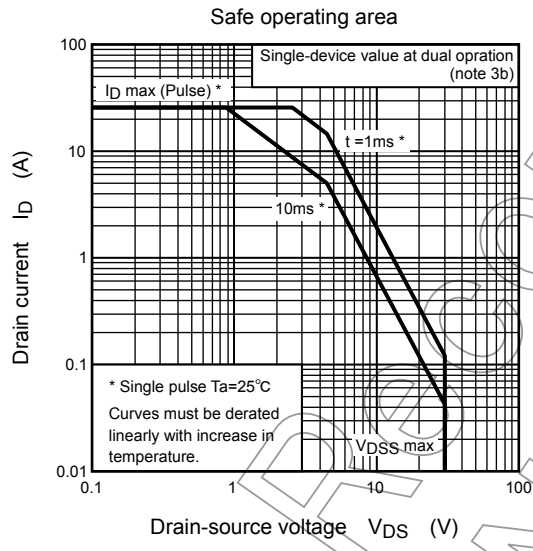
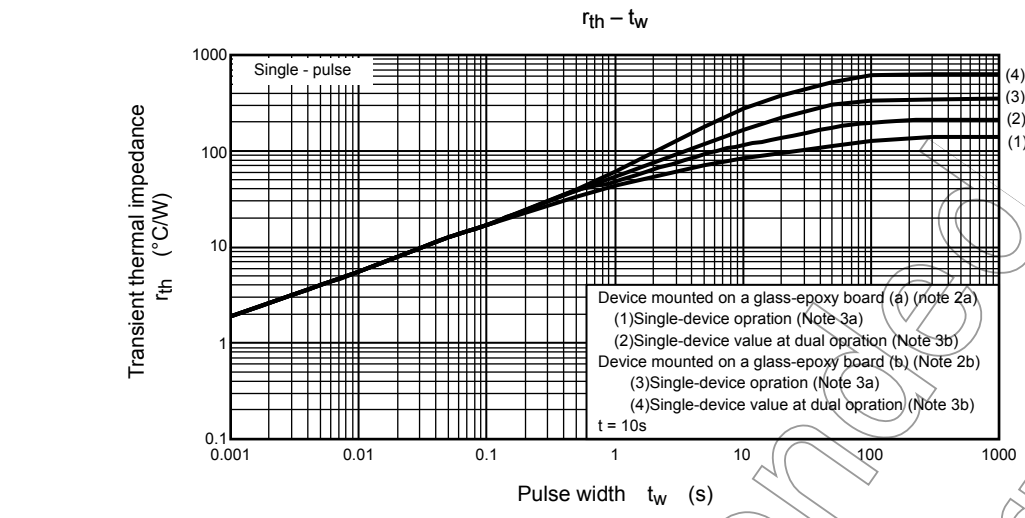
Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		$I_{GSS}$	$V_{GS} = \pm 20 \text{ V}$ , $V_{DS} = 0 \text{ V}$	—	—	$\pm 100$	nA
Drain cutoff current		$I_{DSS}$	$V_{DS} = 30 \text{ V}$ , $V_{GS} = 0 \text{ V}$	—	—	10	$\mu\text{A}$
Drain-source breakdown voltage	$V_{(BR) DSS}$		$I_D = 10 \text{ mA}$ , $V_{GS} = 0 \text{ V}$	30	—	—	V
	$V_{(BR) DSX}$		$I_D = 10 \text{ mA}$ , $V_{GS} = -20 \text{ V}$	15	—	—	
Gate threshold voltage		$V_{th}$	$V_{DS} = 10 \text{ V}$ , $I_D = 0.1 \text{ mA}$	1.3	—	2.3	V
Drain-source ON-resistance	$R_{DS(ON)}$		$V_{GS} = 4.5 \text{ V}$ , $I_D = 3.2 \text{ A}$	—	16.5	23.0	$\text{m}\Omega$
	$R_{DS(ON)}$		$V_{GS} = 10 \text{ V}$ , $I_D = 3.2 \text{ A}$	—	13.6	20.0	
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 10 \text{ V}$ , $I_D = 3.2 \text{ A}$	9.5	19	—	S
Input capacitance		$C_{iss}$	$V_{DS} = 10 \text{ V}$ , $V_{GS} = 0 \text{ V}$ , $f = 1 \text{ MHz}$	—	900	1170	pF
Reverse transfer capacitance		$C_{rss}$		—	65	104	
Output capacitance		$C_{oss}$		—	200	—	
Gate resistance		$R_g$	$V_{DS} = 10 \text{ V}$ , $V_{GS} = 0 \text{ V}$ , $f = 5 \text{ MHz}$	—	2.5	3.6	$\Omega$
Switching time	Rise time	$t_r$		—	2.3	—	ns
	Turn-on time	$t_{on}$		—	7.0	—	
	Fall time	$t_f$		—	9.2	—	
	Turn-off time	$t_{off}$		—	28	—	
Total gate charge (gate-source plus gate-drain) (Note 7)		$Q_g$	$V_{DD} \approx 24 \text{ V}$ , $V_{GS} = 10 \text{ V}$ , $I_D = 6.4 \text{ A}$	—	14	—	nC
			$V_{DD} \approx 24 \text{ V}$ , $V_{GS} = 5 \text{ V}$ , $I_D = 6.4 \text{ A}$	—	7.6	—	
Gate-source charge 1		$Q_{gs1}$	$V_{DD} \approx 24 \text{ V}$ , $V_{GS} = 10 \text{ V}$ , $I_D = 6.4 \text{ A}$	—	2.4	—	
Gate-drain ("Miller") charge		$Q_{gd}$		—	2.5	—	
Gate switch charge		$Q_{SW}$		—	3.4	—	

## Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
Drain reverse current	Pulse (Note 1)	$I_{DRP}$	—	—	—	25.6	A
Forward voltage (diode)		$V_{DSF}$	$I_{DR} = 6.4 \text{ A}$ , $V_{GS} = 0 \text{ V}$	—	—	-1.2	V







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